

PATENT APPLICATION  
Q61045

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Fumiyoishi ONO

Appln. No.: 09/672,776



Confirmation No.: not yet assigned

Group Art Unit: 1765

Filed: September 29, 2000

Examiner: C. Brown

For: COMPOSITION FOR POLISHING METAL ON SEMICONDUCTOR  
METHOD OF USING SAME

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TC 1765 WAIVER AND  
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**AMENDMENT UNDER 37 C.F.R. § 1.111**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

This Amendment is submitted in response to the Office Action dated December 6, 2000, in which the Examiner set a three-month period for response.

Please amend the above-identified application as follows:

**IN THE CLAIMS:**

**Please enter the following amended claims:**

*Sub C*

6. (Amended) A method for polishing a metal film on a semiconductor substrate, comprising the steps of:

    providing a semiconductor substrate comprising a metal film and an insulating film therein;

    providing a polishing composition comprising alumina fine particles containing or not containing aluminum hydrate, a polishing accelerator and water, said alumina fine particles having an  $\alpha$  conversion ratio of from 65 to 90% and a specific surface

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